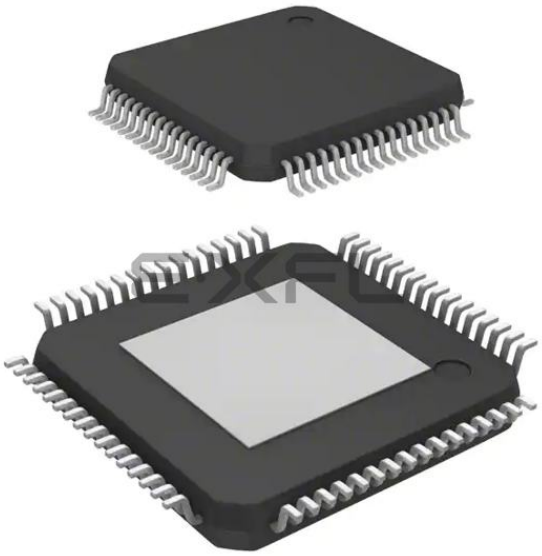
Infineon Technologies - XC2236N16F66LAAKXUMA1 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16/32-Bit
Speed	66MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	38
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-64-6
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xc2236n16f66laakxuma1

16/32-Bit

Architecture

XC2232N, XC2234N, XC2236N, XC2238N

16/32-Bit Single-Chip Microcontroller
with 32-Bit Performance
XC2000 Family / Value Line

Data Sheet

V1.5 2013-02

Microcontrollers

Table of Contents

- On-Chip Peripheral Modules
  - Two synchronizable A/D Converters with up to 9 channels, 10-bit resolution, conversion time below 1 µs, optional data preprocessing (data reduction, range check), broken wire detection
  - 16-channel general purpose capture/compare unit (CC2)
  - Two capture/compare units for flexible PWM signal generation (CCU6x)
  - Multi-functional general purpose timer unit with 5 timers
  - Up to 6 serial interface channels to be used as UART, LIN, high-speed synchronous channel (SPI/QSPI), IIC bus interface (10-bit addressing, 400 kbit/s), IIS interface
  - On-chip MultiCAN interface (Rev. 2.0B active) with up to 256 message objects (Full CAN/Basic CAN) on 6 CAN node
  - On-chip system timer and on-chip real time clock
- Single power supply from 3.0 V to 5.5 V
- Power reduction and wake-up modes with flexible power management
- Programmable watchdog timer and oscillator watchdog
- Up to 40 general purpose I/O lines
- On-chip bootstrap loaders
- Supported by a full range of development tools including C compilers, macro-assembler packages, emulators, evaluation boards, HLL debuggers, simulators, logic analyzer disassemblers, programming boards
- On-chip debug support via Device Access Port (DAP) or JTAG interface
- 64-pin Green LQFP package, 0.5 mm (19.7 mil) pitch

Ordering Information

The ordering code for an Infineon microcontroller provides an exact reference to a specific product. This ordering code identifies:

- the derivative itself, i.e. its function set, the temperature range, and the supply voltage
- the temperature range:
  - SAF-…: -40°C to 85°C
  - SAH-…: -40°C to 110°C
  - SAK-…: -40°C to 125°C
- the package and the type of delivery.

For ordering codes for the XC223xN please contact your sales representative or local distributor.

This document describes several derivatives of the XC223xN group:

Basic Device Types are readily available and
Special Device Types are only available on request.

As this document refers to all of these derivatives, some descriptions may not apply to a specific product, in particular to the special device types.

For simplicity the term **XC223xN** is used for all derivatives throughout this document.

2.1 Pin Configuration and Definition

The pins of the XC223xN are described in detail in **Table 6**, which includes all alternate functions. For further explanations please refer to the footnotes at the end of the table. The following figure summarizes all pins, showing their locations on the four sides of the package.

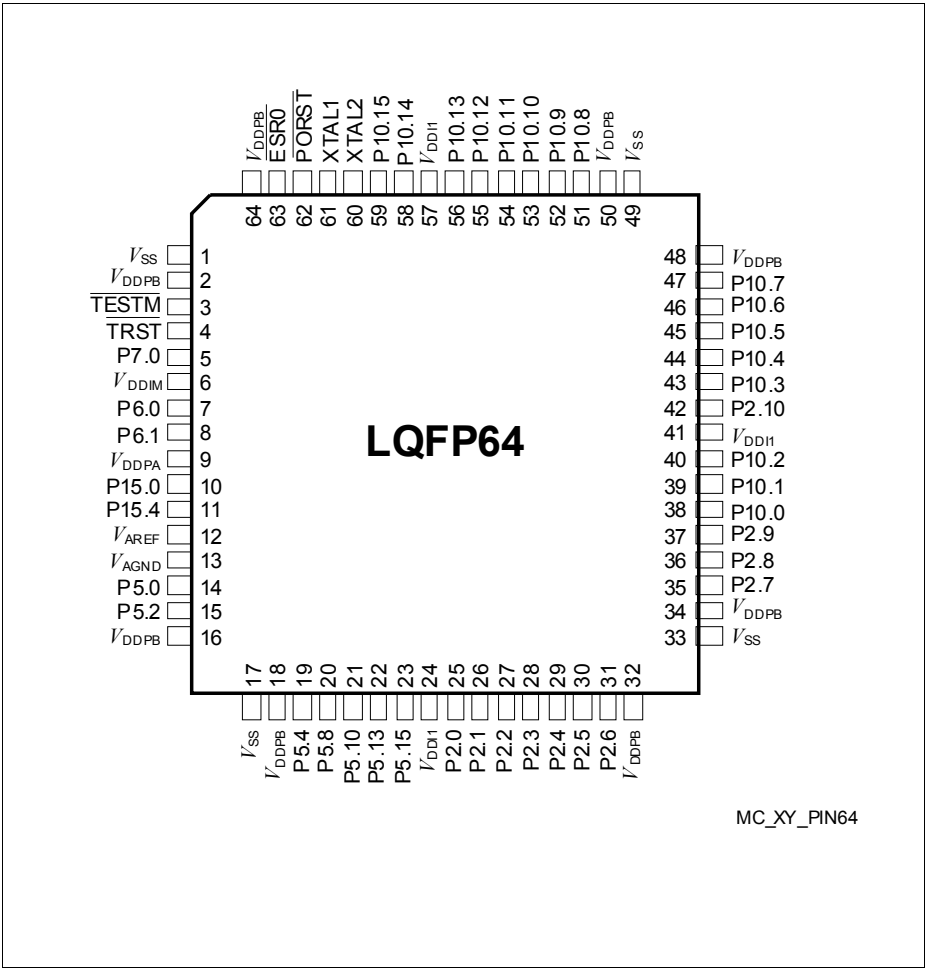

Figure 3 XC223xN Pin Configuration (top view)

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
7	P6.0	O0 / I	DA/A	**Bit 0 of Port 6, General Purpose Input/Output**
	EMUX0	O1	DA/A	**External Analog MUX Control Output 0 (ADC0)**
	TxDC2	O2	DA/A	**CAN Node 2 Transmit Data Output**
	$\overline{\text{BRKOUT}}$	O3	DA/A	**OCDS Break Signal Output**
	ADCx_REQGTyG	I	DA/A	**External Request Gate Input for ADC0/1**
	U1C1_DX0E	I	DA/A	**USIC1 Channel 1 Shift Data Input**
8	P6.1	O0 / I	DA/A	**Bit 1 of Port 6, General Purpose Input/Output**
	EMUX1	O1	DA/A	**External Analog MUX Control Output 1 (ADC0)**
	T3OUT	O2	DA/A	**GPT12E Timer T3 Toggle Latch Output**
	U1C1_DOUT	O3	DA/A	**USIC1 Channel 1 Shift Data Output**
	ADCx_REQTRyE	I	DA/A	**External Request Trigger Input for ADC0/1**
	RxDC2E	I	DA/A	**CAN Node 2 Receive Data Input**
	ESR1_6	I	DA/A	**ESR1 Trigger Input 6**
10	P15.0	I	In/A	**Bit 0 of Port 15, General Purpose Input**
	ADC1_CH0	I	In/A	**Analog Input Channel 0 for ADC1**
11	P15.4	I	In/A	**Bit 4 of Port 15, General Purpose Input**
	ADC1_CH4	I	In/A	**Analog Input Channel 4 for ADC1**
	T6INA	I	In/A	**GPT12E Timer T6 Count/Gate Input**
12	V_{AREF}	-	PS/A	**Reference Voltage for A/D Converters ADC0/1**
13	V_{AGND}	-	PS/A	**Reference Ground for A/D Converters ADC0/1**
14	P5.0	I	In/A	**Bit 0 of Port 5, General Purpose Input**
	ADC0_CH0	I	In/A	**Analog Input Channel 0 for ADC0**
15	P5.2	I	In/A	**Bit 2 of Port 5, General Purpose Input**
	ADC0_CH2	I	In/A	**Analog Input Channel 2 for ADC0**
	TDI_A	I	In/A	**JTAG Test Data Input**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
40	P10.2	O0 / I	St/B	**Bit 2 of Port 10, General Purpose Input/Output**
	U0C0_SCLKOUT	O1	St/B	**USIC0 Channel 0 Shift Clock Output**
	CCU60_CC62	O2	St/B	**CCU60 Channel 2 Output**
	CCU60_CC62INA	I	St/B	**CCU60 Channel 2 Input**
	U0C0_DX1B	I	St/B	**USIC0 Channel 0 Shift Clock Input**
42	P2.10	O0 / I	St/B	**Bit 10 of Port 2, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	U0C0_SELO3	O2	St/B	**USIC0 Channel 0 Select/Control 3 Output**
	CC2_CC23	O3 / I	St/B	**CAPCOM2 CC23IO Capture Inp./ Compare Out.**
	U0C1_DX0E	I	St/B	**USIC0 Channel 1 Shift Data Input**
	CAPINA	I	St/B	**GPT12E Register CAPREL Capture Input**
43	P10.3	O0 / I	St/B	**Bit 3 of Port 10, General Purpose Input/Output**
	CCU60_COUT60	O2	St/B	**CCU60 Channel 0 Output**
	U0C0_DX2A	I	St/B	**USIC0 Channel 0 Shift Control Input**
	U0C1_DX2A	I	St/B	**USIC0 Channel 1 Shift Control Input**
44	P10.4	O0 / I	St/B	**Bit 4 of Port 10, General Purpose Input/Output**
	U0C0_SELO3	O1	St/B	**USIC0 Channel 0 Select/Control 3 Output**
	CCU60_COUT61	O2	St/B	**CCU60 Channel 1 Output**
	U0C0_DX2B	I	St/B	**USIC0 Channel 0 Shift Control Input**
	U0C1_DX2B	I	St/B	**USIC0 Channel 1 Shift Control Input**
	ESR1_9	I	St/B	**ESR1 Trigger Input 9**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
45	P10.5	O0 / I	St/B	**Bit 5 of Port 10, General Purpose Input/Output**
	U0C1_SCLKOUT	O1	St/B	**USIC0 Channel 1 Shift Clock Output**
	CCU60_COUT62	O2	St/B	**CCU60 Channel 2 Output**
	U2C0_DOUT	O3	St/B	**USIC2 Channel 0 Shift Data Output**
	U0C1_DX1B	I	St/B	**USIC0 Channel 1 Shift Clock Input**
46	P10.6	O0 / I	St/B	**Bit 6 of Port 10, General Purpose Input/Output**
	U0C0_DOUT	O1	St/B	**USIC0 Channel 0 Shift Data Output**
	TxDC4	O2	St/B	**CAN Node 4 Transmit Data Output**
	U1C0_SELO0	O3	St/B	**USIC1 Channel 0 Select/Control 0 Output**
	U0C0_DX0C	I	St/B	**USIC0 Channel 0 Shift Data Input**
	U1C0_DX2D	I	St/B	**USIC1 Channel 0 Shift Control Input**
	CCU60_CTRAPA	I	St/B	**CCU60 Emergency Trap Input**
47	P10.7	O0 / I	St/B	**Bit 7 of Port 10, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	CCU60_COUT63	O2	St/B	**CCU60 Channel 3 Output**
	U0C1_DX0B	I	St/B	**USIC0 Channel 1 Shift Data Input**
	CCU60_CCPOS0A	I	St/B	**CCU60 Position Input 0**
	RxDC4C	I	St/B	**CAN Node 4 Receive Data Input**
	T4INB	I	St/B	**GPT12E Timer T4 Count/Gate Input**

Up to 16 Kbytes of on-chip Data SRAM (DSRAM) are used for storage of general user data. The DSRAM is accessed via a separate interface and is optimized for data access.

Note: The actual size of the DSRAM depends on the quoted device type.

2 Kbytes of on-chip Dual-Port RAM (DPRAM) provide storage for user-defined variables, for the system stack, and for general purpose register banks. A register bank can consist of up to 16 word-wide (R0 to R15) and/or byte-wide (RL0, RH0, …, RL7, RH7) General Purpose Registers (GPRs).
The upper 256 bytes of the DPRAM are directly bit addressable. When used by a GPR, any location in the DPRAM is bit addressable.

8 Kbytes of on-chip Stand-By SRAM (SBRAM) provide storage for system-relevant user data that must be preserved while the major part of the device is powered down. The SBRAM is accessed via a specific interface and is powered in domain M.

1024 bytes (2 × 512 bytes) of the address space are reserved for the Special Function Register areas (SFR space and ESFR space). SFRs are word-wide registers which are used to control and monitor functions of the different on-chip units. Unused SFR addresses are reserved for future members of the XC2000 Family. In order to ensure upward compatibility they should either not be accessed or written with zeros.

In order to meet the requirements of designs where more memory is required than is available on chip, up to 12 Mbytes (approximately, see **Table 8**) of external RAM and/or ROM can be connected to the microcontroller. The External Bus Interface also provides access to external peripherals.

The on-chip Flash memory stores code, constant data, and control data. The 320 Kbytes of on-chip Flash memory consist of 1 module of 64 Kbytes (preferably for data storage) and 1 module of 256 Kbytes. Each module is organized in 4-Kbyte sectors. The uppermost 4-Kbyte sector of segment 0 (located in Flash module 0) is used internally to store operation control parameters and protection information.

Note: The actual size of the Flash memory depends on the chosen device type.

Each sector can be separately write protected[1)], erased and programmed (in blocks of 128 Bytes). The complete Flash area can be read-protected. A user-defined password sequence temporarily unlocks protected areas. The Flash modules combine 128-bit read access with protected and efficient writing algorithms for programming and erasing. Dynamic error correction provides extremely high read data security for all read access operations. Access to different Flash modules can be executed in parallel.
For Flash parameters, please see **Section 4.6**.

1) To save control bits, sectors are clustered for protection purposes, they remain separate for programming/erasing.

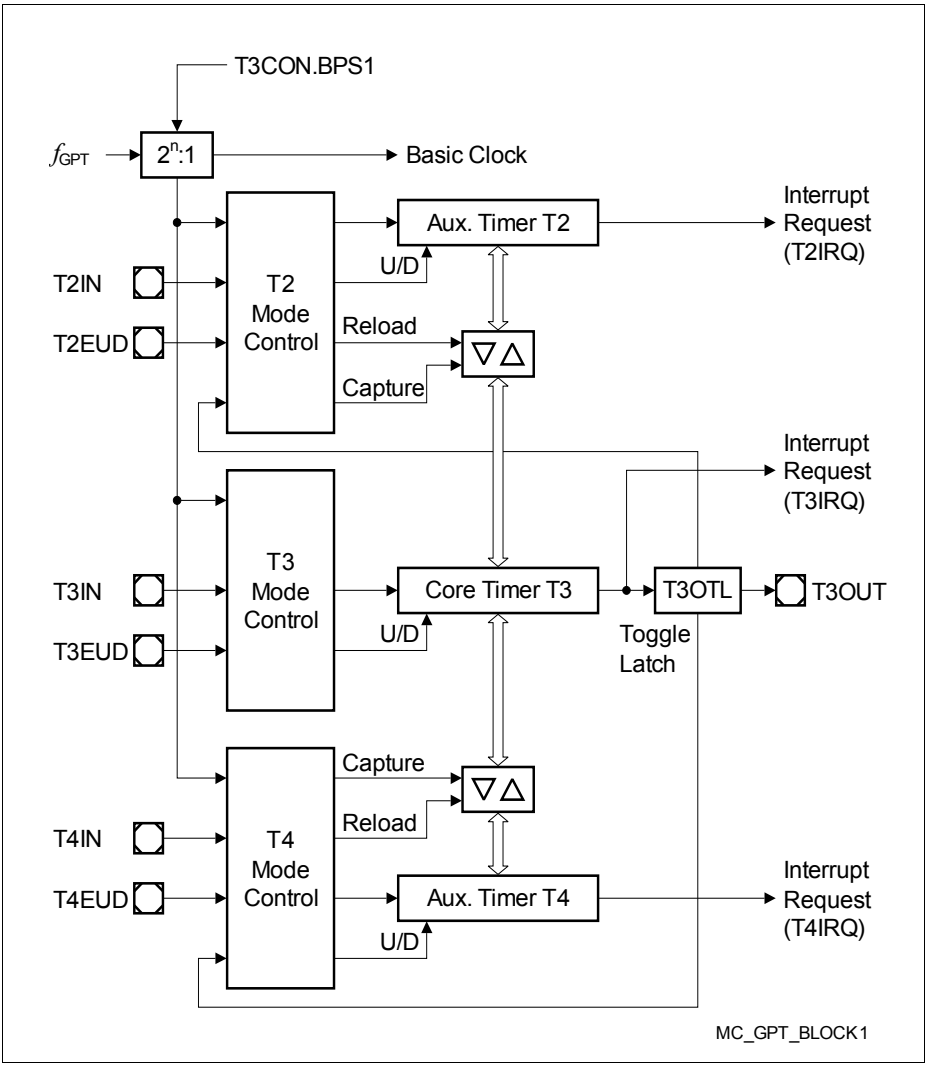

Figure 8 Block Diagram of GPT1

3.17 Parallel Ports

The XC223xN provides up to 40 I/O lines which are organized into 4 input/output ports and 2 input ports. All port lines are bit-addressable, and all input/output lines can be individually (bit-wise) configured via port control registers. This configuration selects the direction (input/output), push/pull or open-drain operation, activation of pull devices, and edge characteristics (shape) and driver characteristics (output current) of the port drivers. The I/O ports are true bidirectional ports which are switched to high impedance state when configured as inputs. During the internal reset, all port pins are configured as inputs without pull devices active.

All port lines have alternate input or output functions associated with them. These alternate functions can be programmed to be assigned to various port pins to support the best utilization for a given application. For this reason, certain functions appear several times in **Table 10**.

All port lines that are not used for alternate functions may be used as general purpose I/O lines.

Table 10 Summary of the XC223xN's Ports

Port	Width	I/O	Connected Modules
P2	11	I/O	CAN, CC2, GPT12E, USIC, DAP/JTAG
P5	7	I	Analog Inputs, CCU6, DAP/JTAG, GPT12E, CAN
P6	2	I/O	ADC, CAN, GPT12E
P7	1	I/O	CAN, GPT12E, SCU, DAP/JTAG, USIC
P10	16	I/O	CCU6, USIC, DAP/JTAG, CAN
P15	2	I	Analog Inputs, GPT12E

7) An overload current (I_{OV}) through a pin injects a certain error current (I_{INJ}) into the adjacent pins. This error current adds to the respective pins leakage current (I_{OZ}). The amount of error current depends on the overload current and is defined by the overload coupling factor K_{OV}. The polarity of the injected error current is inverse compared to the polarity of the overload current that produces it.The total current through a pin is $|I_{TOT}| = |I_{OZ}| + (|I_{OV}| \ K_{OV})$. The additional error current may distort the input voltage on analog inputs.

8) Value is controlled by on-chip regulator

4.2 Voltage Range definitions

The XC223xN timing depends on the supply voltage. If such a dependency exists the timing values are given for 2 voltage areas commonly used. The voltage areas are defined in the following tables.

Table 14 Upper Voltage Range Definition

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage for IO pads and voltage regulators	V_{DDP} SR	4.5	5	5.5	V	

Table 15 Lower Voltage Range Definition

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage for IO pads and voltage regulators	V_{DDP} SR	3.0	3.3	4.5	V	

4.2.1 Parameter Interpretation

The parameters listed in the following include both the characteristics of the XC223xN and its demands on the system. To aid in correctly interpreting the parameters when evaluating them for a design, they are marked accordingly in the column “Symbol”:

CC (**C**ontroller **C**haracteristics):
The logic of the XC223xN provides signals with the specified characteristics.

SR (**S**ystem **R**equirement):
The external system must provide signals with the specified characteristics to the XC223xN.

Table 16 DC Characteristics for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output High voltage[7]	V_{OH} CC	V_{DDP} - 1.0	–	–	V	$I_{OH} \geq I_{OHmax}$
		V_{DDP} - 0.4	–	–	V	$I_{OH} \geq I_{OHnom}$ [8]
Output Low Voltage[7]	V_{OL} CC	–	–	0.4	V	$I_{OL} \leq I_{OLnom}$ [8]
		–	–	1.0	V	$I_{OL} \leq I_{OLmax}$

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): I_{OZ} = 0.05 x $e^{(1.5 + 0.028 \times TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): I_{OZ} = $I_{OZtempmax}$ - (1.6 x DV) (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device.

6) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level.

7) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

8) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

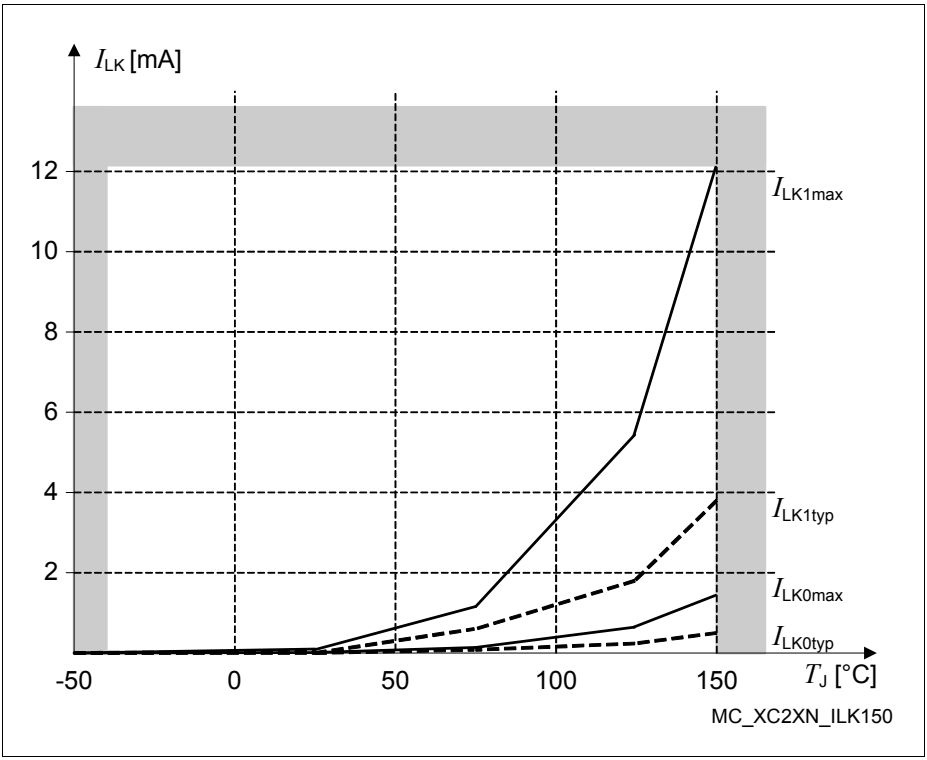

Figure 15 Leakage Supply Current as a Function of Temperature

4.4 Analog/Digital Converter Parameters

These parameters describe the conditions for optimum ADC performance.

Note: Operating Conditions apply.

Table 20 ADC Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Switched capacitance at an analog input	C_{AINSW} CC	–	–	4	pF	not subject to production test [1]
Total capacitance at an analog input	C_{AINT} CC	–	–	10	pF	not subject to production test [1]
Switched capacitance at the reference input	C_{AREFSW} CC	–	–	7	pF	not subject to production test [1]
Total capacitance at the reference input	C_{AREFT} CC	–	–	15	pF	not subject to production test [1]
Differential Non-Linearity Error	$\lvert EA_{DNL}\rvert$ CC	–	0.8	1	LSB	
Gain Error	$\lvert EA_{GAIN}\rvert$ CC	–	0.4	0.8	LSB	
Integral Non-Linearity	$\lvert EA_{INL}\rvert$ CC	–	0.8	1.2	LSB	
Offset Error	$\lvert EA_{OFF}\rvert$ CC	–	0.5	0.8	LSB	
Analog clock frequency	f_{ADCI} SR	0.5	–	16.5	MHz	voltage_range= lower
		0.5	–	20	MHz	voltage_range= upper
Input resistance of the selected analog channel	R_{AIN} CC	–	–	2	kOhm	not subject to production test [1]
Input resistance of the reference input	R_{AREF} CC	–	–	2	kOhm	not subject to production test [1]

4.6 Flash Memory Parameters

The XC223xN is delivered with all Flash sectors erased and with no protection installed.

The data retention time of the XC223xN's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 25 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	2[1)]		$N_{FL\_RD} \leq 1$
		–	–	1[2)]		$N_{FL\_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycles	$t_{RET} \geq$ 20 years
Flash wait states[3)]	$N_{WSFLASH}$ SR	1	–	–		$f_{SYS} \leq$ 8 MHz
		2	–	–		$f_{SYS} \leq$ 13 MHz
		3	–	–		$f_{SYS} \leq$ 17 MHz
		4	–	–		$f_{SYS} >$ 17 MHz
Erase time per sector/page	t_{ER} CC	–	7[4)]	8.0	ms	
Programming time per page	t_{PR} CC	–	3[4)]	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	years	$N_{ER} \leq$ 1,000 cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycles	
Number of erase cycles	N_{ER} SR	–	–	15.000	cycles	$t_{RET} \geq$ 5 years; Valid for Flash module 1 (up to 64 kbytes)
		–	–	1.000	cycles	$t_{RET} \geq$ 20 years

1) The unused Flash module(s) can be erased/programmed while code is executed and/or data is read from only one Flash module or from PSRAM. The Flash module that delivers code/data can, of course, not be erased/programmed.

2) Flash module 1 can be erased/programmed while code is executed and/or data is read from Flash module 0.
3) Value of IMB_IMBCTRL.WSFLASH.
4) Programming and erase times depend on the internal Flash clock source. The control state machine needs a few system clock cycles. This increases the stated durations noticably only at extremely low system clock frequencies.

Access to the XC223xN Flash modules is controlled by the IMB. Built-in prefetch mechanisms optimize the performance for sequential access.

Flash access waitstates only affect non-sequential access. Due to prefetch mechanisms, the performance for sequential access (depending on the software structure) is only partially influenced by waitstates.

Direct Drive

When direct drive operation is selected (SYSCON0.CLKSEL = 11_B), the system clock is derived directly from the input clock signal CLKIN1:

$f_{SYS} = f_{IN}$.

The frequency of f_{SYS} is the same as the frequency of f_{IN}. In this case the high and low times of f_{SYS} are determined by the duty cycle of the input clock f_{IN}.

Selecting Bypass Operation from the XTAL1[1)] input and using a divider factor of 1 results in a similar configuration.

Prescaler Operation

When prescaler operation is selected (SYSCON0.CLKSEL = 10_B, PLLCON0.VCOBY = 1_B), the system clock is derived either from the crystal oscillator (input clock signal XTAL1) or from the internal clock source through the output prescaler K1 (= K1DIV+1):

$f_{SYS} = f_{OSC}$ / K1.

If a divider factor of 1 is selected, the frequency of f_{SYS} equals the frequency of f_{OSC}. In this case the high and low times of f_{SYS} are determined by the duty cycle of the input clock f_{OSC} (external or internal).

The lowest system clock frequency results from selecting the maximum value for the divider factor K1:

$f_{SYS} = f_{OSC}$ / 1024.

4.7.2.1 Phase Locked Loop (PLL)

When PLL operation is selected (SYSCON0.CLKSEL = 10_B, PLLCON0.VCOBY = 0_B), the on-chip phase locked loop is enabled and provides the system clock. The PLL multiplies the input frequency by the factor **F** ($f_{SYS} = f_{IN} \times$ **F**).
F is calculated from the input divider P (= PDIV+1), the multiplication factor N (= NDIV+1), and the output divider K2 (= K2DIV+1):
(**F** = N / (P × K2)).

The input clock can be derived either from an external source at XTAL1 or from the on-chip clock source.

The PLL circuit synchronizes the system clock to the input clock. This synchronization is performed smoothly so that the system clock frequency does not change abruptly.

Adjustment to the input clock continuously changes the frequency of f_{SYS} so that it is locked to f_{IN}. The slight variation causes a jitter of f_{SYS} which in turn affects the duration of individual TCSs.

1) Voltages on XTAL1 must comply to the core supply voltage V_{DDIM}.

4.7.3 External Clock Input Parameters

These parameters specify the external clock generation for the XC223xN. The clock can be generated in two ways:

- By connecting a **crystal or ceramic resonator** to pins XTAL1/XTAL2.
- By supplying an **external clock signal**
  - This clock signal can be supplied either to pin XTAL1 (core voltage domain) or to pin CLKIN1 (IO voltage domain).

If connected to CLKIN1, the input signal must reach the defined input levels V_{IL} and V_{IH}. If connected to XTAL1, a minimum amplitude V_{AX1} (peak-to-peak voltage) is sufficient for the operation of the on-chip oscillator.

Note: The given clock timing parameters (t_1 … t_4) are only valid for an external clock input signal.

Note: Operating Conditions apply.

Table 27 External Clock Input Characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Oscillator frequency	f_{OSC} SR	4	–	40	MHz	Input= Clock Signal
		4	–	16	MHz	Input= Crystal or Ceramic Resonator
XTAL1 input current absolute value	$\|I_{IL}\|$ CC	–	–	20	µA	
Input clock high time	t_1 SR	6	–	–	ns	
Input clock low time	t_2 SR	6	–	–	ns	
Input clock rise time	t_3 SR	–	8	8	ns	
Input clock fall time	t_4 SR	–	8	8	ns	
Input voltage amplitude on XTAL1[1)]	V_{AX1} SR	0.3 x V_{DDIM}	–	–	V	$f_{OSC} \geq$ 4 MHz; $f_{OSC} <$ 16 MHz
		0.4 x V_{DDIM}	–	–	V	$f_{OSC} \geq$ 16 MHz; $f_{OSC} <$ 25 MHz
		0.5 x V_{DDIM}	–	–	V	$f_{OSC} \geq$ 25 MHz; $f_{OSC} \leq$ 40 MHz
Input voltage range limits for signal on XTAL1	V_{IX1} SR	-1.7 + V_{DDIM}	–	1.7	V	[2)]

4.7.4 Pad Properties

The output pad drivers of the XC223xN can operate in several user-selectable modes. Strong driver mode allows controlling external components requiring higher currents such as power bridges or LEDs. Reducing the driving power of an output pad reduces electromagnetic emissions (EME). In strong driver mode, selecting a slower edge reduces EME.

The dynamic behavior, i.e. the rise time and fall time, depends on the applied external capacitance that must be charged and discharged. Timing values are given for a capacitance of 20 pF, unless otherwise noted.

In general, the performance of a pad driver depends on the available supply voltage V_{DDP}. Therefore the following tables list the pad parameters for the upper voltage range and the lower voltage range, respectively.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 28 is valid under the following conditions: $V_{DDP} \leq$ 5.5 V; V_{DDP}typ. 5 V; $V_{DDP} \geq$ 4.5 V

Table 28 Standard Pad Parameters for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum output driver current (absolute value)[1)]	I_{Omax} CC	–	–	4.0	mA	Driver_Strength = Medium
		–	–	10	mA	Driver_Strength = Strong
		–	–	0.5	mA	Driver_Strength = Weak
Nominal output driver current (absolute value)	I_{Onom} CC	–	–	1.0	mA	Driver_Strength = Medium
		–	–	2.5	mA	Driver_Strength = Strong
		–	–	0.1	mA	Driver_Strength = Weak

Table 29 Standard Pad Parameters for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum output driver current (absolute value)[1)]	I_{Omax} CC	–	–	2.5	mA	Driver_Strength = Medium
		–	–	10	mA	Driver_Strength = Strong
		–	–	0.5	mA	Driver_Strength = Weak
Nominal output driver current (absolute value)	I_{Onom} CC	–	–	1.0	mA	Driver_Strength = Medium
		–	–	2.5	mA	Driver_Strength = Strong
		–	–	0.1	mA	Driver_Strength = Weak